

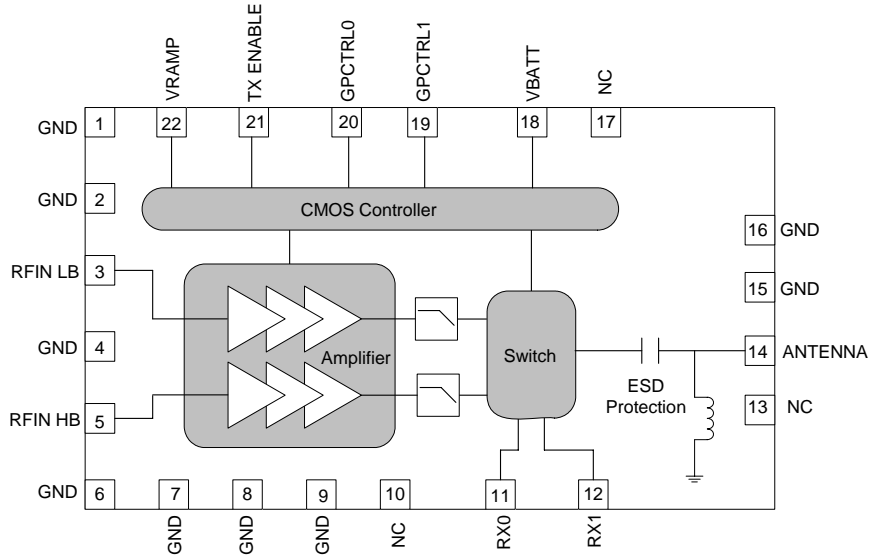


Features

- Enhanced Performance Transmit Module
- No External Routing
- High Efficiency at Rated P_{OUT}
GSM850=40%
EGSM900=41%
DCS1800=37%
PCS1900=37%
- V_{BATT}=3.5V
- Low RX Insertion Loss
- Two Symmetrical RX Ports
- 0dBm to 6dBm Drive Level, >50dB of Dynamic Range
- Integrated Power-Flattening Circuit for Lower Power Variation under Mismatch Conditions
- V_{BATT} Tracking Circuit for Improved Switching Spectrum Performance under Low V_{BATT} Conditions

Applications

- 3V Quad-Band GSM/GPRS Handsets
- GSM850/EGSM900/DCS1800/PCS1900 Products
- GPRS Class 12 Compliant
- Portable Battery-Powered Equipment



Functional Block Diagram

Product Description

The RF7171 is a quad-band (GSM850/EGSM900/DCS1800/PCS1900) GSM/GPRS, Class 12 compliant transmit module with two interchangeable receive ports. This transmit module builds upon RFMD's leading power amplifier with PowerStar® integrated power control technology, pHEMT switch technology, and integrated transmit filtering for best-in-class harmonic performance. The results are high performance, reduced solution size, and ease of implementation. The device is designed for use as the final portion of the transmitter section in a GSM850/EGSM900/DCS1800/PCS1900 handset and eliminates the need for a PA-to-antenna switch module matching network.

The RF7171 features RFMD's latest integrated power-flattening circuit which significantly reduces current and power variation into load mismatch. Additionally, a V_{BATT} tracking feature is incorporated to maintain switching performance as supply voltage decreases. The RF7171 also integrates an ESD filter to provide excellent ESD protection at the antenna port. The RF7171 is designed to provide maximum efficiency at rated P_{OUT}.

Ordering Information

RF7171	Quad-Band GSM850/EGSM900/DCS1800/PCS1900 Transmit Module
RF7171SB	Transmit Module 5-Piece Sample Pack
RF7171PCBA-41X	Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

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|--|--------------------------------------|--|-----------------------------------|
| <input checked="" type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input checked="" type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input checked="" type="checkbox"/> Si CMOS | <input type="checkbox"/> RF MEMS |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | <input type="checkbox"/> LDMOS |

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Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage	-0.3 to +6.0	V
Power Control Voltage (V_{RAMP})	-0.3 to +1.8	V
Input RF Power	+10	dBm
Max Duty Cycle	50	%
Output Load VSWR	20:1	
Operating Case Temperature	-20 to +85	°C
Storage Temperature	-55 to +150	°C



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
ESD					
ESD Antenna Port			8	kV	IEC 61000-4-2
ESD All Ports			1000	V	HBM, JESD22-A114
			1000	V	CDM, JEDEC JESD22-C101
Overall Power Control V_{RAMP}					
Power Control "ON"			1.8	V	Max. P_{OUT}
Power Control "OFF"		0.25		V	Min. P_{OUT}
V_{RAMP} Input Capacitance		15	20	pF	DC to 200kHz
V_{RAMP} Input Current			10	μ A	$V_{RAMP} = V_{RAMP, MAX}$
Power Control Range		50		dB	$V_{RAMP} = 0.25V$ to $V_{RAMP, MAX}$
Overall Power Supply					
Power Supply Voltage	3.0	3.5	4.8	V	Operating Limits
Power Supply Current		40	80	μ A	$P_{IN} < -30dBm$, TX Enable=Low, $V_{RAMP} = 0.25V$, Temp = -20°C to +85°C, $V_{BATT} = 4.8V$.
Overall Control Signals					
GpCtrl0/1/2 "Low"	0	0	0.5	V	
GpCtrl0/1/2 "High"	1.25	2.0	V_{BATT}	V	
GpCtrl0/1/2 "High Current"		1	2	μ A	
TX Enable "Low"	0	0	0.5	V	
TX Enable "High"	1.25	2.0	V_{BATT}	V	
TX Enable "High Current"		1	2	μ A	
RF Port Input and Output Impedance		50		Ω	

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
GSM850 Band					Nominal conditions unless otherwise stated. All unused ports are terminated. $V_{BATT}=3.5V$, $P_{IN}=3dBm$, Temp = +25 °C, TX Enable = High, $V_{RAMP}=1.8V$. TX Mode: GpCtrl1 = High, GpCtrl0 = Low, Duty Cycle = 25%, Pulse Width = 1154 μ S
Operating Frequency Range	824		849	MHz	
Input Power	0	3	6	dBm	Full P_{OUT} guaranteed at minimum drive level.
Input VSWR		1.8:1	2.5:1		Over P_{OUT} range (5 dBm to 33 dBm)
Maximum Output Power	33.0	34.2		dBm	Nominal conditions.
	31.0	34.1		dBm	$V_{BATT}=3.1V$ to 4.8V, $P_{IN}=0dBm$ to 6dBm, Temp = -20 °C to +85 °C, Duty Cycle = 50%, Pulse Width = 2308mS, $V_{RAMP}\leq 1.8V$.
Minimum Power Into 3:1 VSWR	29.5	31.4		dBm	The measured delivered output power to the load with the mismatch loss already taken into account with 1dB variation margin.
Efficiency	36	40		%	Set $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=33dBm$
2nd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=33dBm$.
3rd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=33dBm$.
All other harmonics up to 12.75GHz			-33	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=33dBm$.
Non-harmonic Spurious up to 12.75GHz			-36	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=33dBm$, also over all power levels (5dBm to 33dBm).
Forward Isolation 1		-59	-41	dBm	TX Enable Low, $P_{IN}=6dBm$, $V_{RAMP}=0.25V$.
Forward Isolation 2		-27	-15	dBm	TX Enable High, $P_{IN}=6dBm$, $V_{RAMP}=0.25V$.
Output Noise Power		-86.5	-82	dBm	869MHz to 894MHz. $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=33dBm$, RBW = 100 kHz.
		-117.5	-74	dBm	1930MHz to 1990MHz. $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=33dBm$, RBW = 100 kHz.
Output Load VSWR Stability (Spurious Emissions)			-36	dBm	VSWR = 12:1, all phase angles (Set $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}\leq 33dBm$ into 50 Ω load; load switched to VSWR = 12:1).
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 20:1, all phase angles (Set $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}\leq 33dBm$ into 50 Ω load; load switched to VSWR = 20:1).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
EGSM900 Band					Nominal conditions unless otherwise stated. All unused ports are terminated. $V_{BATT}=3.5V$, $P_{IN}=3\text{ dBm}$, Temp = +25 °C, TX Enable = High, $V_{RAMP}=1.8V$. TX Mode: GpCtrl1 = High, GpCtrl0 = Low, Duty Cycle = 25%, Pulse Width = 1154 μs
Operating Frequency Range	880		915	MHz	
Input Power	0	3	6	dBm	Full P_{OUT} guaranteed at minimum drive level.
Input VSWR		1.7:1	2.5:1		Over P_{OUT} range (5dBm to 33dBm).
Maximum Output Power	33.0	34.1		dBm	Nominal conditions.
	31.0	34.0		dBm	$V_{BATT}=3.1V$ to 4.8V, $P_{IN}=0\text{ dBm}$ to 6dBm, Temp = -20 °C to +85 °C, Duty Cycle = 50%, Pulse Width = 2308mS, $V_{RAMP}\leq 1.8V$.
Minimum Power Into 3:1 VSWR	30.0	31.4		dBm	The measured delivered output power to the load with the mismatch loss already taken into account with 1dB variation margin.
Efficiency	36	41		%	Set $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$
2nd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$.
3rd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$.
All other harmonics up to 12.75GHz			-33	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$.
Non-harmonic Spurious up to 12.75GHz			-36	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$, also over all power levels (5dBm to 33dBm).
Forward Isolation 1		-61	-41	dBm	TX Enable Low, $P_{IN}=6\text{ dBm}$, $V_{RAMP}=0.25V$.
Forward Isolation 2		-28	-15	dBm	TX Enable High, $P_{IN}=6\text{ dBm}$, $V_{RAMP}=0.25V$.
Output Noise Power		-86	-77	dBm	925 MHz to 935 MHz. $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$, RBW = 100 kHz.
		-87	-83	dBm	935 MHz to 960 MHz. $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$, RBW = 100 kHz.
		-117.5	-87	dBm	1805 MHz to 1880 MHz. $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=33\text{ dBm}$, RBW = 100 kHz.
Output Load VSWR Stability (Spurious Emissions)			-36	dBm	VSWR = 12:1, all phase angles (Set $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}\leq 33\text{ dBm}$ into 50 Ω load; load switched to VSWR = 12:1).
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 20:1, all phase angles (Set $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}\leq 33\text{ dBm}$ into 50 Ω load; load switched to VSWR = 20:1).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
DCS1800 Band					Nominal conditions unless otherwise stated. All unused ports are terminated. $V_{BATT}=3.5V$, $P_{IN}=3dBm$, Temp = +25 °C, TX Enable = High, $V_{RAMP}=1.8V$. TX Mode: GpCtrl1 = High, GpCtrl0 = High, Duty Cycle = 25%, Pulse Width = 1154 μ S
Operating Frequency Range	1710		1785	MHz	
Input Power	0	3	6	dBm	Full P_{OUT} guaranteed at minimum drive level.
Input VSWR		1.5:1	2.5:1		Over P_{OUT} range (0dBm to 30dBm).
Maximum Output Power	30.0	31.5		dBm	Nominal conditions.
	28.0	31.5		dBm	$V_{BATT}=3.0V$ to 4.8V, $P_{IN}=0dBm$ to 6dBm, Temp = -20 °C to +85 °C, Duty Cycle = 50%, Pulse Width = 2308mS, $V_{RAMP}\leq 1.8V$.
Minimum Power Into 3:1 VSWR	27.0	28.5		dBm	The measured delivered output power to the load with the mismatch loss already taken into account with 1dB variation margin.
Efficiency	32	37		%	Set $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$
2nd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$.
3rd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$.
4th Harmonic		-36	-30	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$.
All other harmonics up to 12.75GHz			-33	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$.
Non-harmonic Spurious up to 12.75GHz			-36	dBm	$V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$, also over all power levels (0dBm to 30dBm).
Forward Isolation 1		-64	-53	dBm	TX Enable Low, $P_{IN}=6dBm$, $V_{RAMP}=0.25V$.
Forward Isolation 2		-28	-15	dBm	TX Enable High, $P_{IN}=6dBm$, $V_{RAMP}=0.25V$.
Output Noise Power		-101	-77	dBm	925MHz to 935MHz. $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$, RBW = 100 kHz.
		-100	-83	dBm	935MHz to 960MHz. $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$, RBW = 100 kHz.
		-94	-79	dBm	1805MHz to 1880MHz. $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}=30dBm$, RBW = 100 kHz.
Output Load VSWR Stability (Spurious Emissions)			-36	dBm	VSWR = 12:1, all phase angles (Set $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}\leq 30dBm$ into 50 Ω load; load switched to VSWR = 12:1).
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 20:1, all phase angles (Set $V_{RAMP}=V_{RAMP RATED}$ for $P_{OUT}\leq 30dBm$ into 50 Ω load; load switched to VSWR = 20:1).

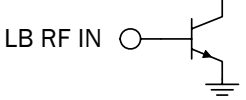
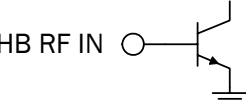
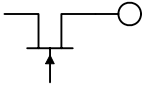
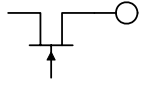
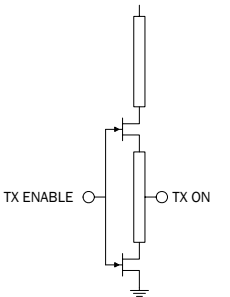
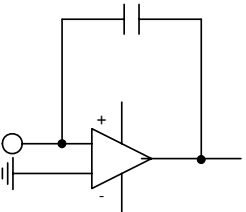
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
PCS1900 Band					Nominal conditions unless otherwise stated. All unused ports are terminated. $V_{BATT}=3.5V$, $P_{IN}=3\text{ dBm}$, Temp = +25 °C, TX Enable = High, $V_{RAMP}=1.8V$. TX Mode: GpCtrl1 = High, GpCtrl0 = High, Duty Cycle = 25%, Pulse Width = 1154 μ S
Operating Frequency Range	1850		1910	MHz	
Input Power	0	3	6	dBm	Full P_{OUT} guaranteed at minimum drive level.
Input VSWR		1.4:1	2.5:1		Over P_{OUT} range (5dBm to 30dBm).
Maximum Output Power	30	31.2		dBm	Nominal conditions.
	28	31.2		dBm	$V_{BATT}=3.0V$ to 4.8V, $P_{IN}=0\text{ dBm}$ to 6dBm, Temp = -20 °C to +85 °C, Duty Cycle = 50%, Pulse Width = 2308mS, $V_{RAMP}\leq 1.8V$.
Minimum Power Into 3:1 VSWR	27	28.5		dBm	The measured delivered output power to the load with the mismatch loss already taken into account with 1dB variation margin.
Efficiency	32	37		%	Set $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$
2nd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$.
3rd Harmonic		-40	-33	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$.
4th Harmonic		-36	-30	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$.
All other harmonics up to 12.75GHz			-33	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$.
Non-harmonic Spurious up to 12.75GHz			-36	dBm	$V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$, also over all power levels (5dBm to 30dBm).
Forward Isolation 1		-66	-53	dBm	TX Enable Low, $P_{IN}=6\text{ dBm}$, $V_{RAMP}=0.25V$.
Forward Isolation 2		-30	-15	dBm	TX Enable High, $P_{IN}=6\text{ dBm}$, $V_{RAMP}=0.25V$.
Output Noise Power		-102	-82	dBm	869MHz to 894MHz. $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$, RBW = 100kHz.
		-94	-74	dBm	1930MHz to 1990MHz. $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}=30\text{ dBm}$, RBW = 100kHz.
Output Load VSWR Stability (Spurious Emissions)			-36	dBm	VSWR = 12:1, all phase angles (Set $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}\leq 30\text{ dBm}$ into 50 Ω load; load switched to VSWR = 12:1).
Output Load VSWR Ruggedness	No damage or permanent degradation to device				VSWR = 20:1, all phase angles (Set $V_{RAMP}=V_{RAMP\text{ RATED}}$ for $P_{OUT}\leq 30\text{ dBm}$ into 50 Ω load; load switched to VSWR = 20:1).

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
RX Section					Nominal conditions unless otherwise stated. VBATT=3.5V, PIN=-10dBm, Temp=+25 °C, TX Enable=Low, VRAMP=0.2V, RX0 Mode: GpCtrl0=Low, GpCtrl1=High, RX1 Mode: GpCtrl0=High, GpCtrl1=High RX Frequencies: GSM850=869MHz to 894MHz EGSM900=925MHz to 960MHz DCS1800=1805MHz to 1880MHz PCS1900=1930MHz to 1990MHz
Insertion Loss GSM850/EGSM900 ANT-RX0/1		1.0	1.3	dB	See Note 1.
In-Band Ripple GSM850/EGSM900 ANT-RX0/1		0.05	0.2	dB	
Input VSWR GSM850/EGSM900 ANT-RX0/1		1.3:1	1.5:1		
Insertion Loss DCS1800/PCS1900 ANT-RX0/1		1.3	1.6	dB	See Note 1.
In-Band Ripple DCS1800/PCS1900 ANT-RX0/1		0.1	0.2	dB	
Input VSWR DCS1800/PCS1900 ANT-RX0/1		1.5:1	1.8:1		
TX Section					
Switch Leakage P _{OUT} at RX Port GSM850/EGSM900 ANT-RX0/RX1		-18	-10	dBm	GSM850 TX mode: Freq=824MHz to 849MHz, EGSM900 TX mode: Freq=880MHz to 915MHz, GpCtrl1=High, GpCtrl0=Low, V _{RAMP} =V _{RAMP RATED} for P _{OUT} =33dBm at antenna port. See Note 2.
Switch Leakage P _{OUT} at RX Port DCS1800/PCS1900 ANT-RX0/RX1		-15	-10		DCS1800 TX mode: Freq=1710MHz to 1785MHz, PCS1900 TX mode: Freq=1850MHz to 1910MHz, GpCtrl1=High, GpCtrl0=High, V _{RAMP} =V _{RAMP RATED} for P _{OUT} =30dBm at antenna port. See Note 2.

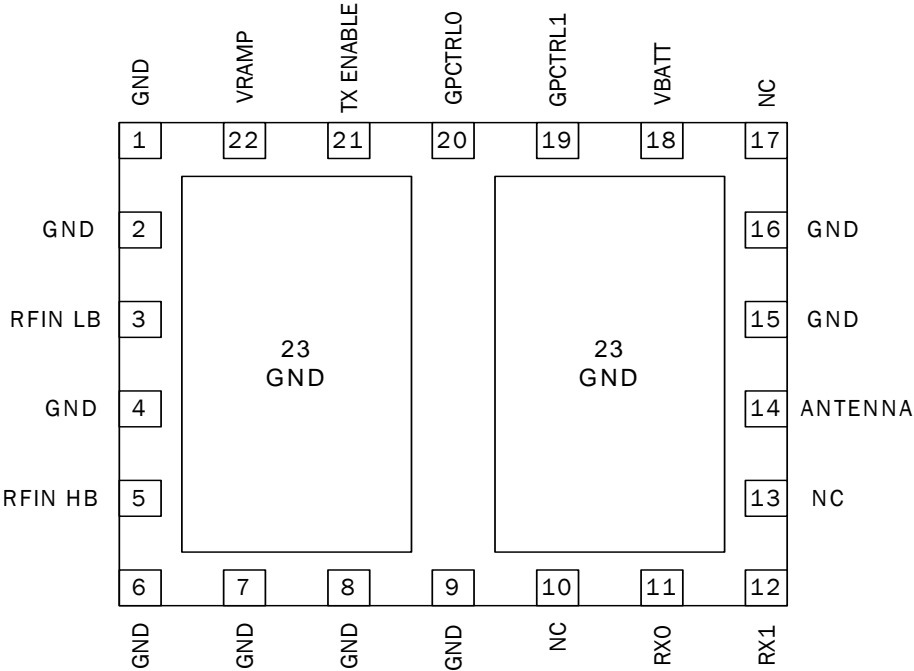
Note 1: Some improvement can be obtained in these measurements by optimally matching the antenna/receiver ports.

Note 2: Isolation specification set to ensure at least the following isolation at rated power. Calculation example: Switch Leakage=P_{OUT} at Antenna - P_{OUT} at RX Port. LB switch leakage=33-(-18)=51dB, HB switch leakage=30-(-15)=45dB.

TX ENABLE	GpCtrl1	GpCtrl0	TX Module Mode
0	0	0	Low Power Mode (Standby)
0	1	0	RX0
0	1	1	RX1
1	1	0	GSM850/900 TX Mode
1	1	1	DCS1800/PCS1900 TX Mode

Pin	Function	Description	Interface Schematic
1	GND	Ground.	
2	GND	Ground.	
3	RF IN LB	RF input to the GSM850/EGSM900 bands. This is a 50Ω input.	
4	GND	Ground.	
5	RF IN HB	RF input to the DCS1800/PCS1900 bands. This is a 50Ω input.	
6	GND	Ground.	
7	GND	Ground.	
8	GND	Ground.	
9	GND	Ground.	
10	NC	Not connected.	
11	RX0	RX0 of antenna switch. This port is interchangeable with any other RX port.	
12	RX1	RX1 of antenna switch. This port is interchangeable with any other RX port.	
13	NC	Not connected.	
14	Antenna	Antenna port. This is a 50Ω output.	
15	GND	Ground.	
16	GND	Ground.	
17	NC	Not connected.	
18	VBATT	Power supply for the module. This should be connected to the battery terminal using as wide a trace as possible.	
19	GPCTRL1	Control pin that together with GpCtrl0 selects the band of operation.	
20	GPCTRL0	Control pin that together with GpCtrl1 selects the band of operation.	
21	TX ENABLE	This signal enables the PA module for operation with a logic high. The switch is put in TX mode determined by GpCtrl0 and GpCtrl1.	
22	VRAMP	VRAMP ramping signal from DAC. A simple RC filter is integrated into the RF7171 module. VRAMP may or may not require additional filtering depending on the baseband selected.	

Pin Out



Theory of Operation

Product Description

The RF7171 is a quad-band transmit module (TXM) with fully-integrated power control functionality, harmonic filtering, band selectivity, and TX/RX switching. The TXM is self-contained, having 50Ω I/O terminals and two interchangeable RX ports allowing dual-band RX operation. The power control function eliminates all power control circuitry, including directional couplers, diode detectors, and power control ASICs, etc. The power control capability provides 50dB of continuous control range and 70dB of total control range, using a DAC-compatible, analog voltage input. The TX Enable feature provides for PA activation (TX mode) or RX mode/standby. Internal switching provides a low-loss, low-distortion path from the antenna port to the TX path (or RX port) while maintaining proper isolation.

Overview

The RF7171 simplifies the phone design by eliminating the need for the complicated control loop, harmonic filters, and TX/RX switch along with their associated matching components. The power control loop can be driven directly from the DAC output in the baseband circuit. The module has two RX ports for GSM850/EGSM900/DCS1800/PCS1900 operation. The two RX ports can be used interchangeably. To control the mode of operation there are three logic control signals: TX Enable, GpCtrl0, and GpCtrl1. RF7171 offers high efficiency at the rated P_{OUT} as backed-off efficiency is improved in this TXM.

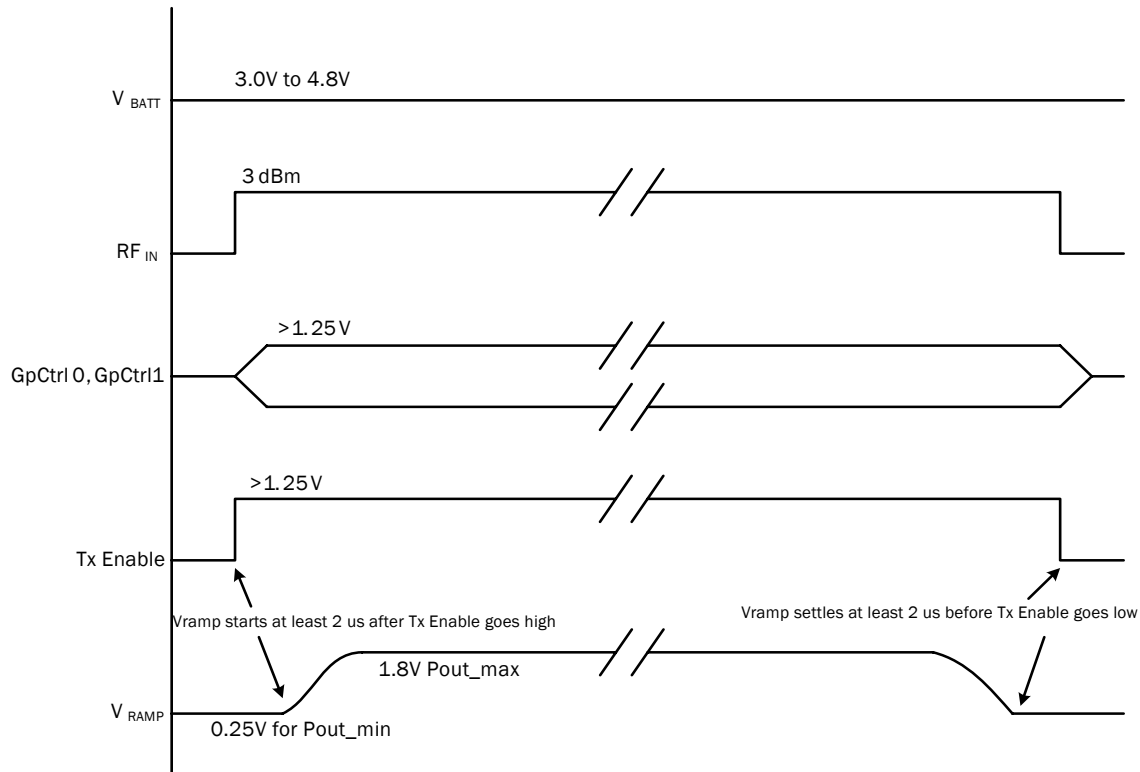
Power Ramping and Timing

The RF7171 should be powered on according to the power-on sequence below. It is designed to prevent operation of the amplifier under conditions that could cause damage to the device or erratic operation.

There are some setup times associated with the control signals of the RF7171. The most important of these is the settling time between TXEN going high and when V_{RAMP} can begin to increase. This time is often referred to as the "pedestal" and is required so that the internal power control loop and bias circuitry can settle after being turned on. The RF7171 requires at least $2\mu s$ or two quarter-bit times for proper settling of the power control loop.

The power-down sequence is in opposite order of the power-on sequence. As described in the figure below, V_{BATT} is applied first to provide bias to the silicon control chip. Then the RF drive is applied. Finally, when TXEN is high, The V_{RAMP} signal is held at a constant 0.25V, and $2\mu s$ later, V_{RAMP} begins to ramp up. The shape of V_{RAMP} is important for maintaining the switching transients. The basic shape of the ramping function should be raised cosine to achieve best transient performance.

Power On Sequence



RF7171 Timing Diagram

Power on sequence

1. Apply V_{BATT} .
2. Apply GpCtrl0, GpCtrl1, RFIN, and TX Enable.
3. Apply V_{RAMP} at least $2\mu S$ after TX Enable.
4. The Power Down Sequence in opposite order of the Power On Sequence.

Power Flattening and V_{BATT} Tracking

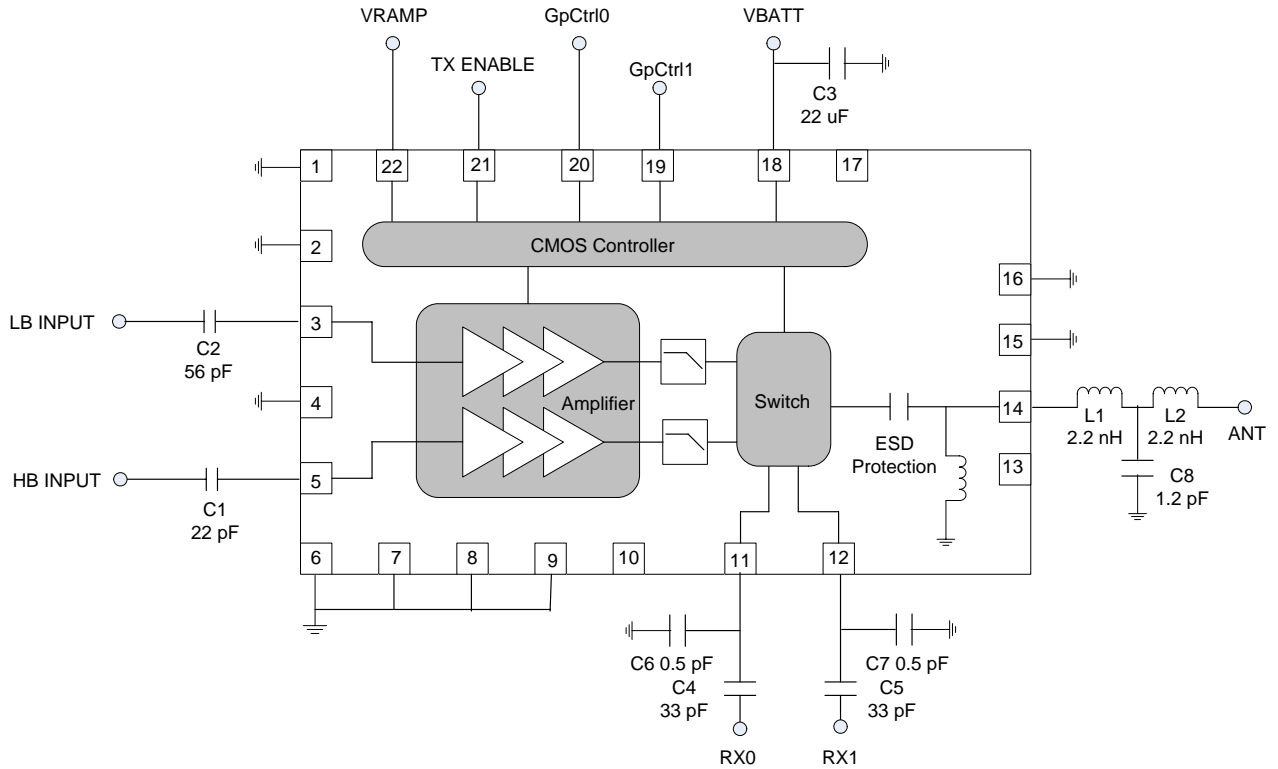
The RF7171 has an integrated power flattening circuit that reduces the amount of current variation when a mismatch is presented to the output of the PA. When a mismatch is presented to the output of the PA its output impedance is varied and could present a load that will increase output power. As the output power increases so does the current consumption. The current consumption can become very high if not monitored and limited. The power flattening circuit is integrated onto the CMOS controller and requires no input from user.

Into a mismatch, the current varies as the phase changes. The power flattening circuit monitors current through an internal sense resistor. As the current changes the loop is adjusted in order to maintain current. The result is flatter power and reduced current into mismatch.

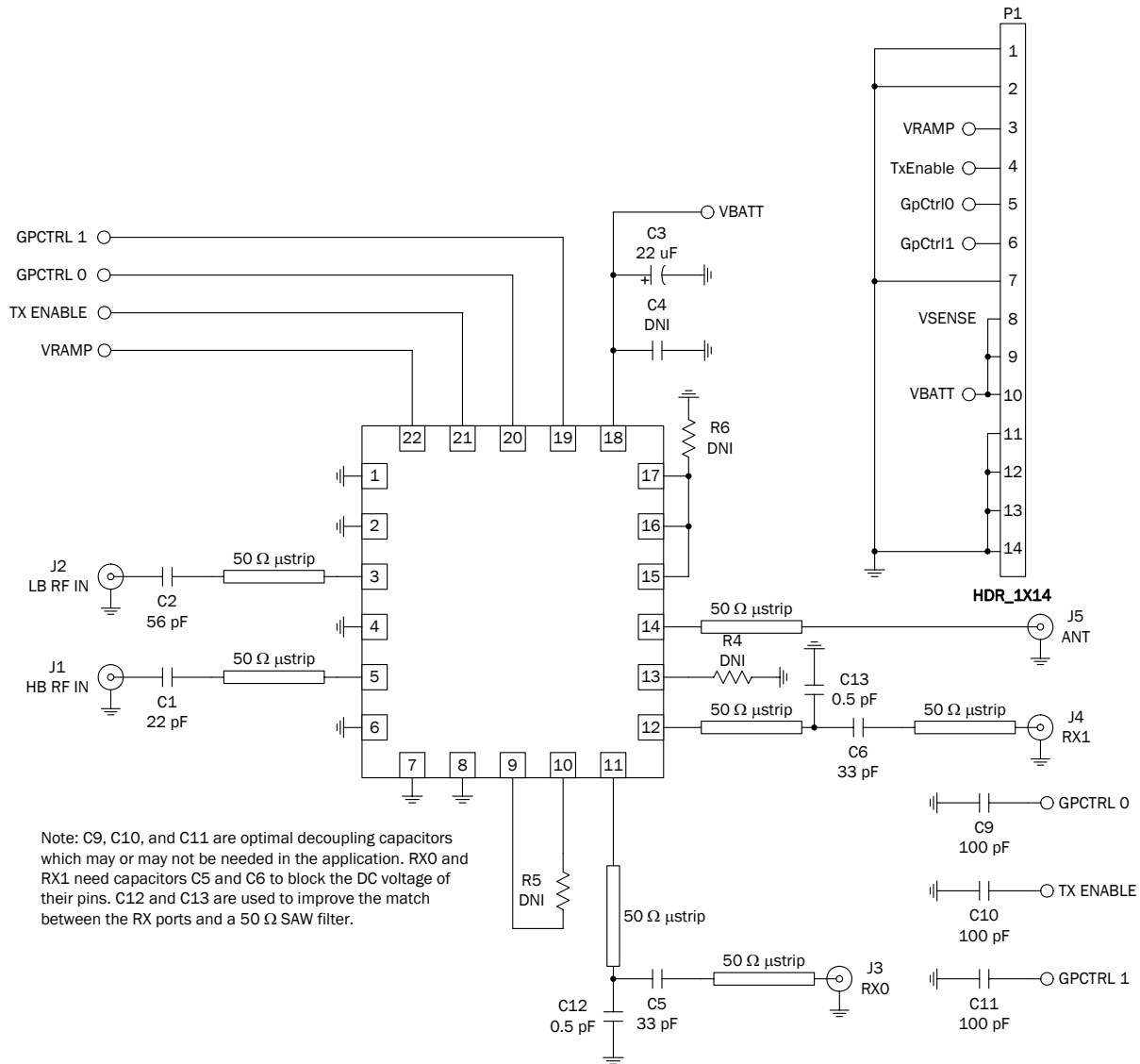
The RF7171 also incorporates a V_{BATT} tracking feature that eliminates the need for the transceiver/baseband to regulate the ramping signal as the supply voltage decreases. The internal circuit monitors the supply voltage and adjusts the ramping signal such that the switching spectrum is minimally impacted.

Application Schematic

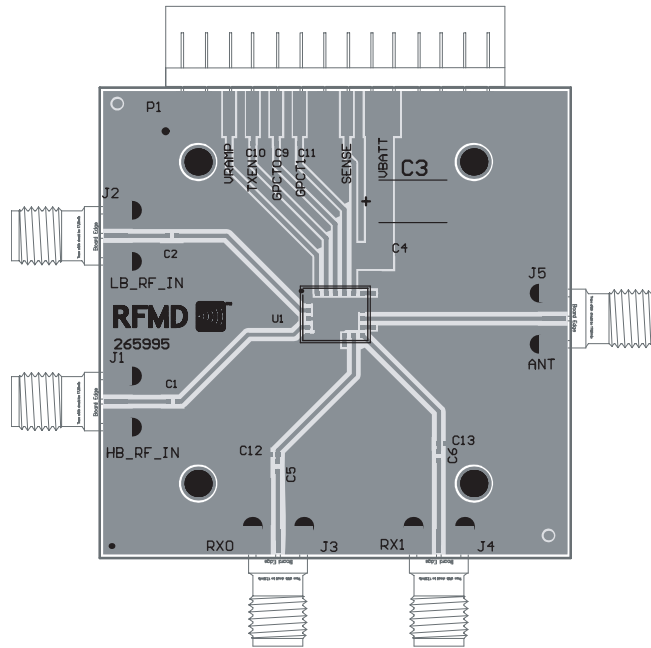
*All inputs, outputs, and antenna traces are 50 Ω micro strip.
 **VBATT capacitor value may change depending on application.
 ***RX0 and RX1 usually connect to SAW filters; C4 and C5 are used to block dc voltage present on the RX ports. C6 and C7 are used to match the RX ports to a 50 Ω filter.
 ****If placing an attenuation network on the input to the power amplifier, ensure that it is positioned on the transceiver side of capacitor C1 (or C2) to prevent adversely affecting the base biasing of the power amplifier.
 *****L1, L2, and C8 is a suggested external LPF to suppress higher order harmonics. Actual component values will depend on the application.



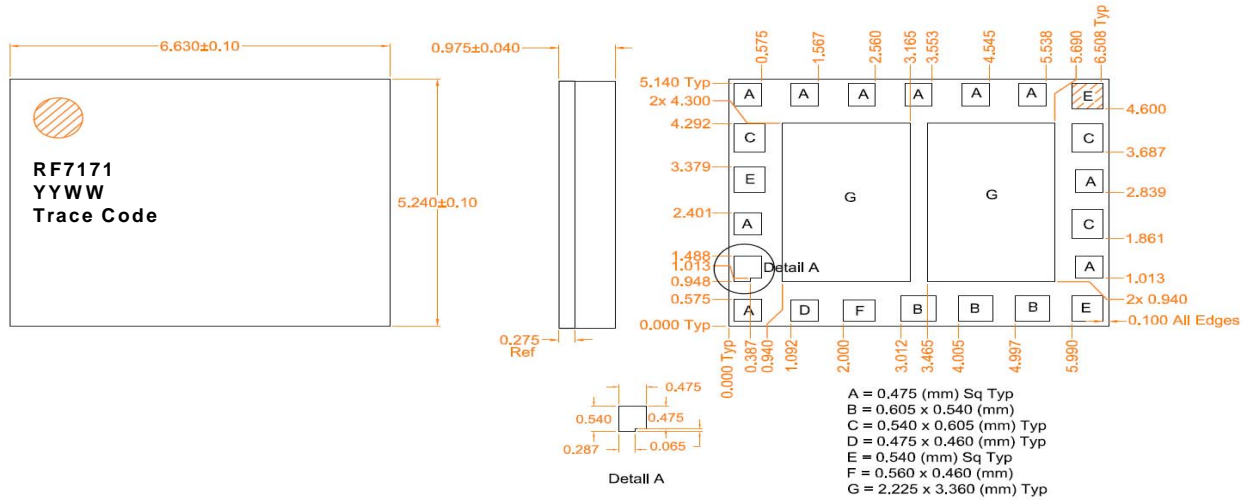
Evaluation Board Schematic



Evaluation Board Layout
Board Size: 2.0" x 2.0"



Package Drawing



Notes:

YY indicates year, WW indicates work week, and Trace Code is a sequential number assigned at device assembly.

Shaded areas represent Pin 1 location.

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PCB Design Requirements

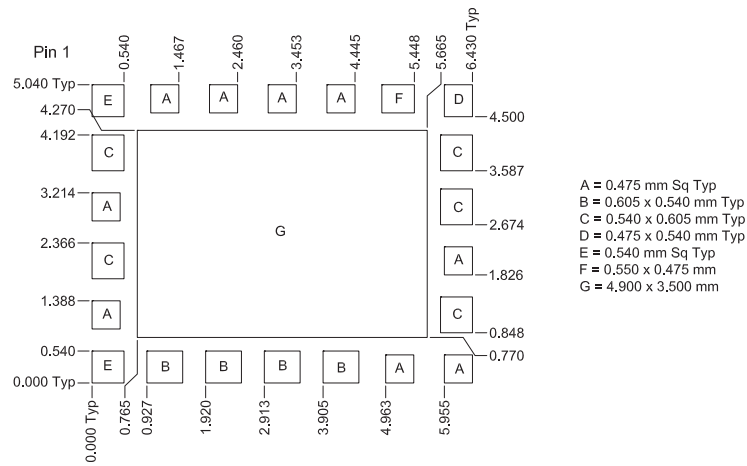
PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3µinch to 8µinch gold over 180µinch nickel.

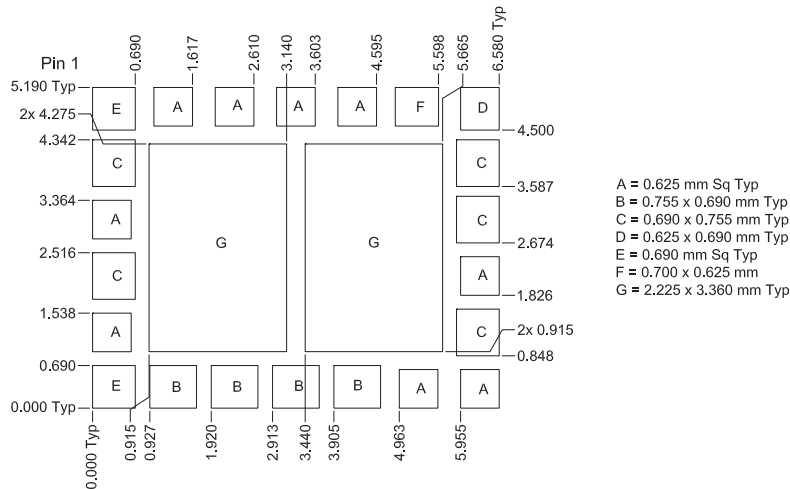
PCB Land Pattern Recommendation

PCB land patterns for RFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

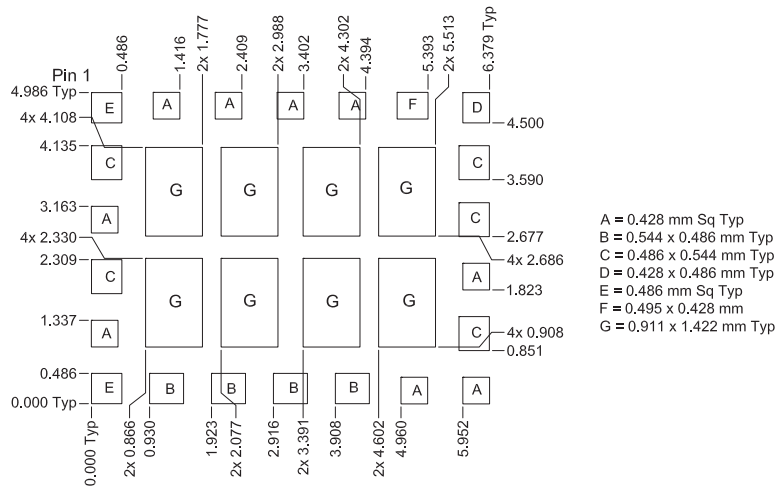
PCB Metal Land



Solder Mask Pattern



Stencil Pattern



Tape and Reel

Carrier tape basic dimensions are based on EIA 481. The pocket is designed to hold the part for shipping and loading onto SMT manufacturing equipment, while protecting the body and the solder terminals from damaging stresses. The individual pocket design can vary from vendor to vendor, but width and pitch will be consistent.

Carrier tape is wound or placed onto a shipping reel either 330mm (13 inches) in diameter or 178mm (7 inches) in diameter. The center hub design is large enough to ensure the radius formed by the carrier tape around it does not put unnecessary stress on the parts.

Prior to shipping, moisture sensitive parts (MSL level 2a-5a) are baked and placed into the pockets of the carrier tape. A cover tape is sealed over the top of the entire length of the carrier tape. The reel is sealed in a moisture barrier ESD bag with the appropriate units of desiccant and a humidity indicator card, which is placed in a cardboard shipping box. It is important to note that unused moisture sensitive parts need to be resealed in the moisture barrier bag. If the reels exceed the exposure limit and need to be rebaked, most carrier tape and shipping reels are not rated as bakeable at 125 °C. If baking is required, devices may be baked according to section 4, table 4-1, of Joint Industry Standard IPC/JEDEC J-STD-033.

The table below provides information for carrier tape and reels used for shipping the devices described in this document.

Tape and Reel

RFMD Part Number	Reel Diameter Inch (mm)	Hub Diameter Inch (mm)	Width (mm)	Pocket Pitch (mm)	Feed	Units per Reel
RF7171TR13	13 (330)	4 (102)	12	8	Single	2500
RF7171TR7	7 (178)	2.4 (61)	12	8	Single	750

Unless otherwise specified, all dimension tolerances per EIA-481.

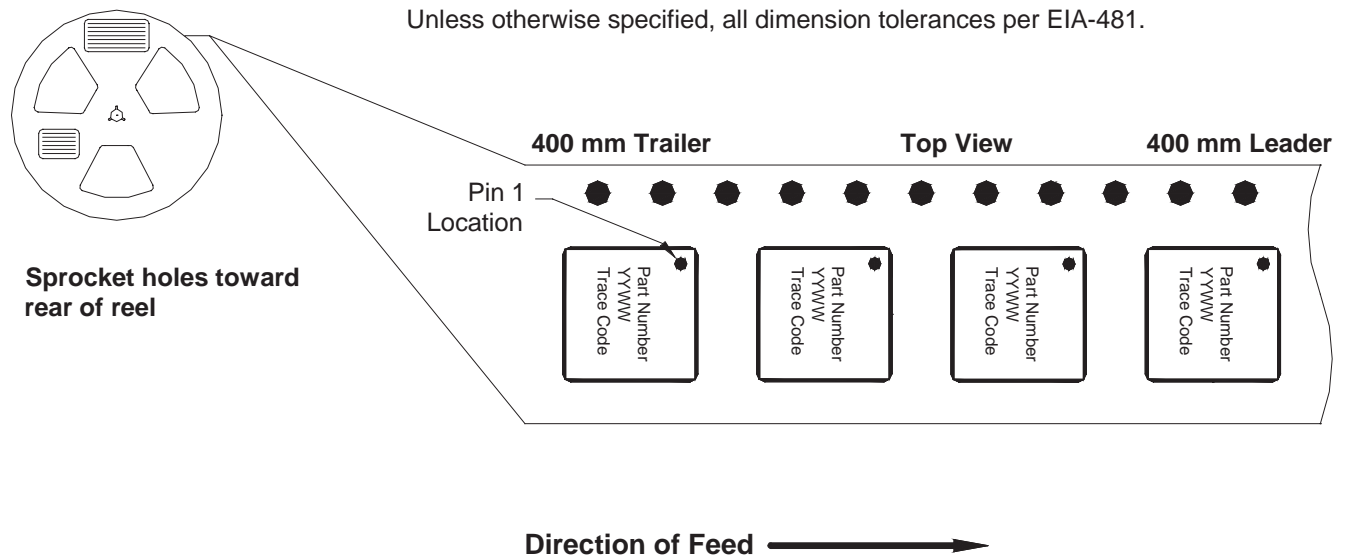


Figure 1. 5.24mmx6.63mm (Carrier Tape Drawing with Part Orientation)

RoHS* Banned Material Content

RoHS Compliant: Yes
 Package total weight in grams (g): 0.121
 Compliance Date Code: -
 Bill of Materials Revision: -
 Pb Free Category: e4

Bill of Materials	Parts Per Million (PPM)					
	Pb	Cd	Hg	Cr VI	PBB	PBDE
Die	0	0	0	0	0	0
Molding Compound	0	0	0	0	0	0
Lead Frame	0	0	0	0	0	0
Die Attach Epoxy	0	0	0	0	0	0
Wire	0	0	0	0	0	0
Solder Plating	0	0	0	0	0	0

This RoHS banned material content declaration was prepared solely on information, including analytical data, provided to RFMD by its suppliers, and applies to the Bill of Materials (BOM) revision noted above.

* DIRECTIVE 2002/95/EC OF THE EUROPEAN PARLIAMENT AND OF THE COUNCIL of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment